YFW 佑风微

Trench MOS Barrier Schottky Rectifier

Reverse Voltage - 200 V

Forward Current - 5 A

FEATURES

- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead free in comply with EU RoHS 2011/65/EU directives

MECHANICAL DATA

- Case: DO-201AD/DO-27
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.98g / 0.0345oz

Maximum Ratings (Per Leg) at Ta=25°C unless otherwise specified

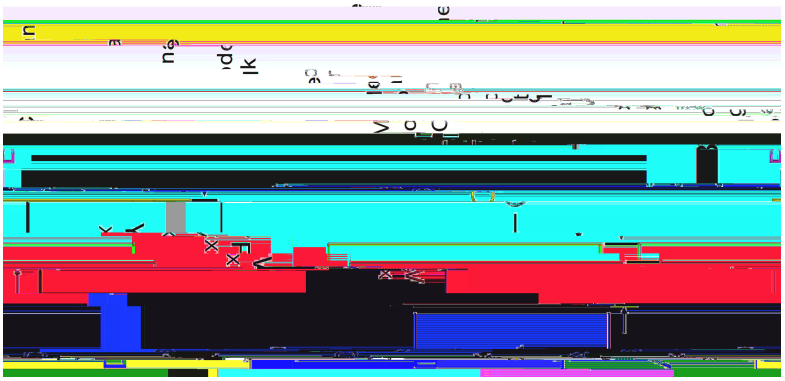
Parameter		Symbols	Value	Units
Maximum Repetitive Peak Reverse Voltage		V_{RRM}	200	V
Maximum RMS voltage		V_{RMS}	200	V
Maximum DC Blocking Voltage		V_{DC}	200	V
Maximum Average Forward Rectified Current	Per diode	$I_{F(AV)}$	5	A
Peak Forward Surge Current, 8.3ms Single Half Sine-wave superimposed on rated load per diode		I_{FSM}	100	A
Operating Temperature Range		T_J	-55 ~ +150	°C
Storage Temperature Range		T_{STG}	-55 ~ +150	°C
Typical Thermal Resistance Per diode(munted on FR-4 PCB)	DO-27	$R_{\theta JC}$	22	°C/W

Note1: Thermal resistance from Junction to case per leg mounted on heatsink.

Electrical Characteristics (Per Leg) unless otherwise specified

Characteristics		Symbols	Value		Units
Forward Voltage Drop(Note2)		V_F	Typ	Max	V
at I_F=3A Instantaneous forward voltage per diode	TA=25°C		0.79	0.83	
	TA=125°C		0.68	-	
at I_F=5A Instantaneous forward voltage per diode	TA=25°C		0.84	-	
	TA=125°C		0.79	-	
Instantaneous reverse current per diode at rated reverse voltage	TA=25°C	I_R	-	2	uA
	TA=125°C		-	80	mA

	bulk	250PCS/500PCS/Box 25000PCS/Carton
	braid	1000PCS/1250PCS/Box 10000PCS/Carton/12500PCS/Carton



A	-	9.50	-	0.370
B	-	6.40	-	0.250
C	1.20	1.30	0.048	0.052
D	25.4	-	1.00	-

The information presented in this document is for reference only. GuangDong Youfeng Microelectronics

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